

SHANGHAI SUNRISE ELECTRONICS CO., LTD.

RC10S01 THRU RC10S10

SILICON SILASTIC CELL RECTIFIER

TECHNICAL SPECIFICATION

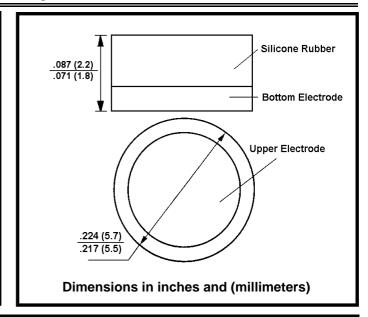
VOLTAGE: 100 TO 1000V CURRENT: 10A

FEATURES

- Low cost
- High surge capability
- Solderable electrode surfaces
- Ideal for hybrids

MECHANICAL DATA

 Polarity: Bottom or upper electrode denotes cathode according to the notice in package



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

outlett by 2070)								
RATINGS	SYMBOL	RC10S 01	RC10S 02	RC10S 04	RC10S 06	RC10S 08	RC10S 10	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current $(T_a=55^{\circ}C)$ (Note 2)	I _{F(AV)}	10						Α
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I _{FSM}	400						Α
Maximum Instantaneous Forward Voltage (at rated forward current)	V_{F}	1.0						V
Maximum DC Reverse Current T _a =25°C		10						μΑ
(at rated DC blocking voltage) T _a =150°C	I _R			500			μΑ	
Typical Junction Capacitance (Note 1)	C_J	300						pF
Typical Thermal Resistance (Note 3)	R _θ (ja)	1						°C/W
Storage and Operation Junction Temperature	T_{STG}, T_{J}	-50 to +150						°C

Note:

- 1. Measured at 1 MHz and applied voltage of $4.0V_{\rm dc}$
- 2. When mounted to heat sink from body.
- 3. Thermal resistance from junction to ambient.